



2811

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE RECEIVED

In re Patent Application of:)
CROCE ET AL.)
Serial No. 09/839,596)
Confirmation No. 1496)
Filing Date: April 20, 2001)
For: RESURF LDMOS INTEGRATED)
STRUCTURE)

) Examiner: O. Nadav
) Art Unit: 2811

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TECHNOLOGY CENTER 2800

#131 Amend
O. Nadav
1/18/03

RESPONSE TO NOTICE OF NON-COMPLIANT AMENDMENT

Director, U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

Responsive to the Notice of Non-Compliant Amendment mailed on December 10, 2002, please enter the amendments and remarks set out below.

In the Claims:

Please amend Claim 14 as follows:

14. (Amended) A lateral diffused metal oxide semiconductor (LDMOS) integrated device comprising:

a semiconductor substrate;

a drain region of a first conductivity type adjacent said semiconductor substrate and comprising a superficial buffer region being more heavily doped than adjacent portions of said drain region;

said superficial buffer region having a dopant concentration of about 5×10^{16} to 5×10^{17} atoms cm^{-3} and the adjacent portions of said drain region having a dopant concentration of about 2.5×10^{15} to 2.5×10^{16} atoms cm^{-3} ;

a body region surrounded by said superficial buffer region and having a second conductivity type; and

a source region in said body region and having the